



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Ken INOUE et al.

Serial No.: 09/667,706

Group Art Unit: 2811

*Filed: September 22, 2000

Examiner: Douglas W. Owens

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Honorable Commissioner of Patents
Washington, D.C. 20231

4-30-02

T. Flowers

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AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated January 17, 2002, please amend the above-identified application as follows:

IN THE TITLE:

Please amend the title to read as follows:

-- METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE HAVING
A MEMORY CELL SECTION AND AN ADJACENT CIRCUIT SECTION --

IN THE SPECIFICATION:

Please amend the specification as follows:

On page 12, amend paragraph 3 starting on line 18 to read as follows:

-- What distinguishes the present invention from the conventional techniques the most is the fact that, even in the memory cell region of the DRAM section, there are formed the S/D regions with a high dopant concentration defined as n^+ . When silicide is formed on the S/D regions with such a high dopant concentration, good ohmic contacts can be formed. Further, because the junction becomes deeper, the junction leakage current is hardly generated even if silicide is formed over all the surfaces of the S/D regions. In contrast with this, when silicide is formed on conventional low dopant-concentration regions (n^-), Schottkey contacts are formed therebetween, which is not adequate for the purpose of